

BTB24-800BW 25A TRIAC

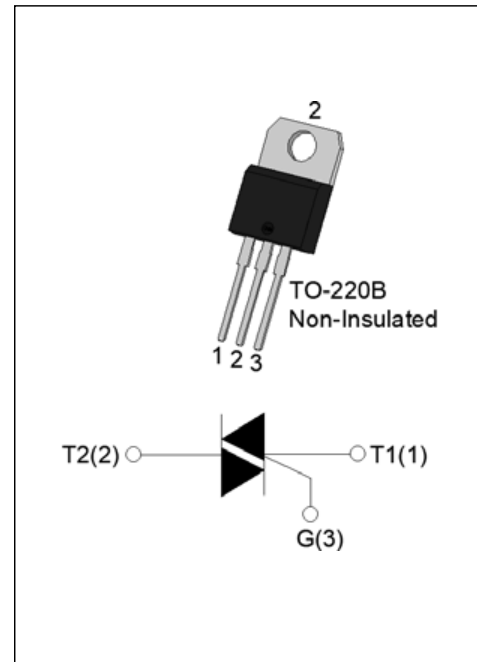
Rev.A.2.0

DESCRIPTION

The BTB24-800BW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. BTB24-800BW snubberless triac is especially recommended for use on inductive loads. Package TO-220B is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	25	A
V_{DRM}/V_{RRM}	800	V
$I_{GT\ I/II/III}$	50/50/50	mA


ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	$^{\circ}C$
Operating junction temperature range	T_j	-40-125	$^{\circ}C$
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	800	V
RMS on-state current ($T_c \leq 100^{\circ}C$)	$I_{T(RMS)}$	25	A
Non repetitive surge peak on-state current (full cycle , $t_p=20ms$, $T_j=25^{\circ}C$)	I_{TSM}	250	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6ms$, $T_j=25^{\circ}C$)		275	
I^2t value for fusing ($t_p=10ms$, $T_j=25^{\circ}C$)	I^2t	340	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=125^{\circ}C$)	di/dt	100	$A/\mu s$
Peak gate current ($t_p=20\mu s$, $T_j=125^{\circ}C$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^{\circ}C$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^{\circ}C$; non-repetitive, off-state)	V_{pp}	2.5	kV

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ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33\Omega$	I - II -III	MAX.	50	mA
V_{GT}		I - II -III	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3K\Omega$	I - II -III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III	MAX.	80	mA
		II		100	
I_H	$I_T=500\text{mA}$		MAX.	75	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125^\circ\text{C}$		MIN.	2000	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=20V/\mu\text{s}$ $T_j=125^\circ\text{C}$		MIN.	25	A/ms
t_{on}	$I_G=80\text{mA}$ $I_A=400\text{mA}$ $I_R=40\text{mA}$ $T_j=25^\circ\text{C}$		TYP.	10	μs
t_{off}				70	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=35A$ $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^\circ\text{C}$	0.75	V
R_D	Dynamic resistance	$T_j=125^\circ\text{C}$	18	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
I_{RRM}		$T_j=125^\circ\text{C}$	2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	0.7	$^\circ\text{C}/W$
$R_{th(j-a)}$	junction to ambient (DC)	60	$^\circ\text{C}/W$

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FIG.1 Maximum power dissipation versus RMS on-state current

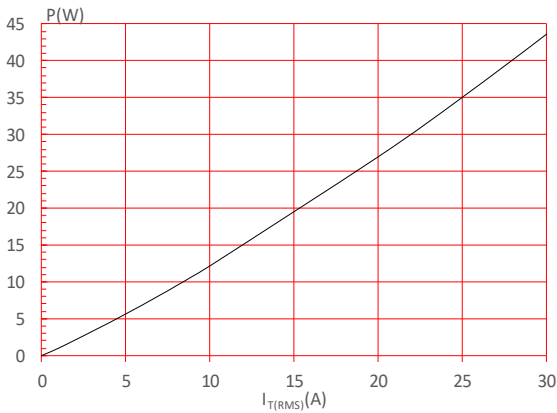


FIG.3: Surge peak on-state current versus number of cycles

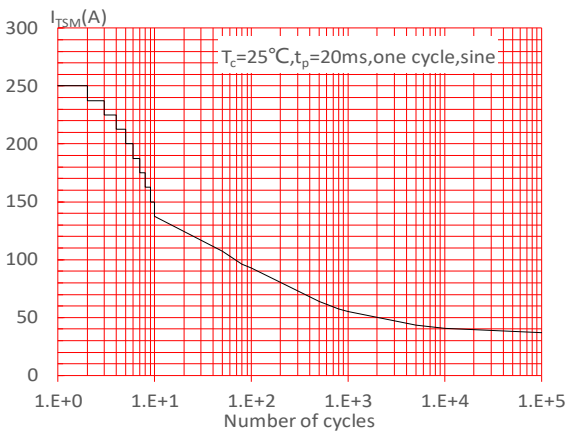


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

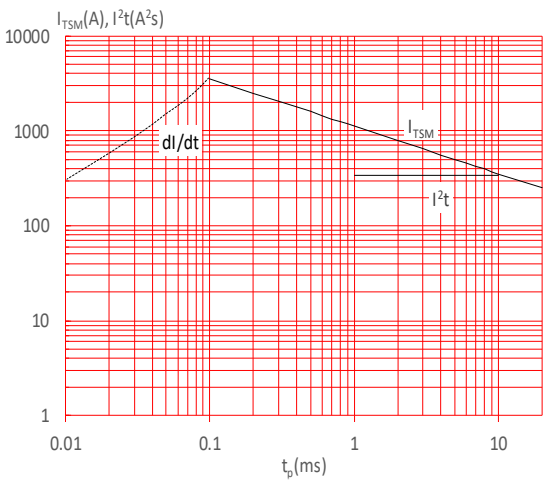


FIG.2: RMS on-state current versus case temperature

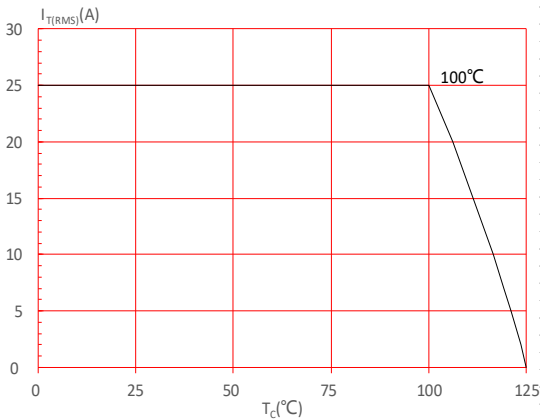


FIG.4: On-state characteristics

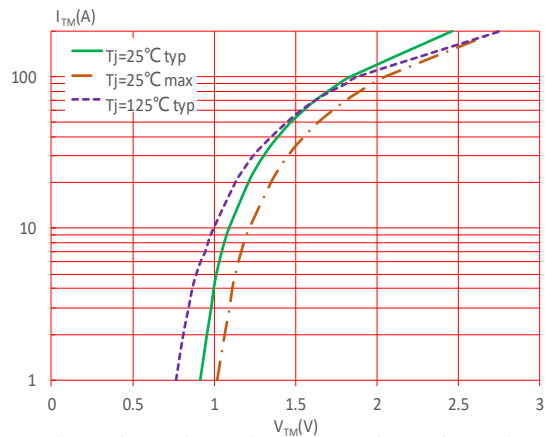
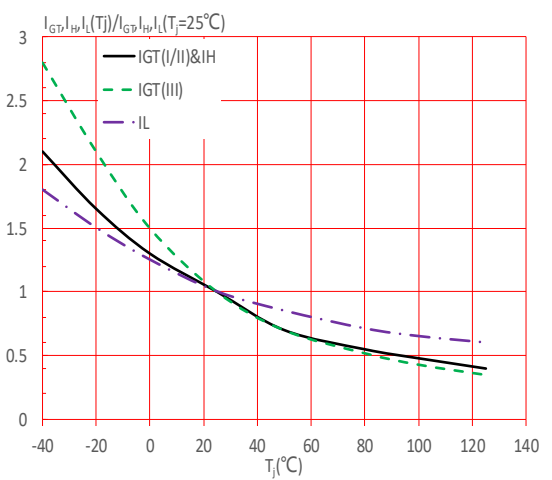


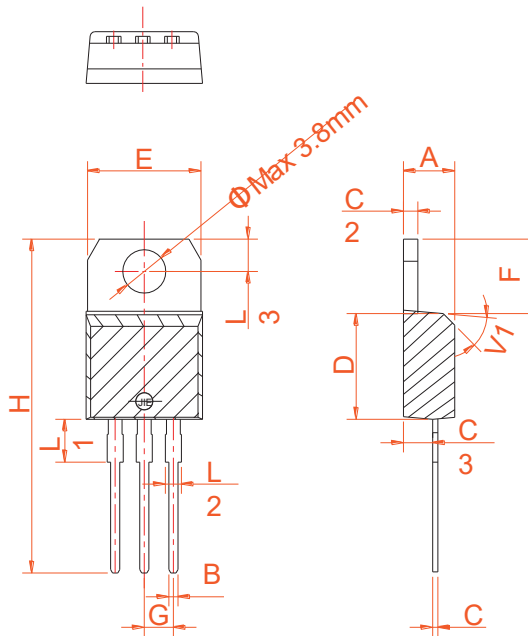
FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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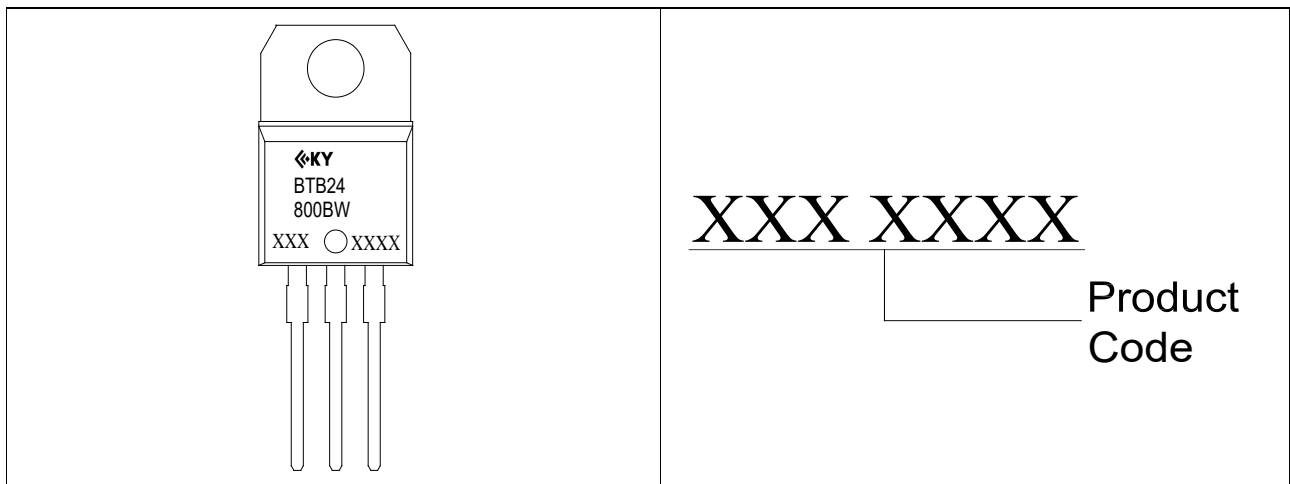
PACKAGE MECHANICAL DATA



TO-220B Non-Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

MARKING



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PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220B	TUBE	50	1,000	5,000

Document Revision History

Date	Revision	Changes
Jun.22, 2025	A.2.0	Last updated

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